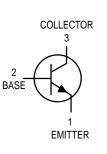
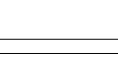
High Voltage Transistor NPN Silicon





BF844



MAXIMUM RATINGS

Symbol	Value	Unit	
VCEO	400	Vdc	
VCBO	450	Vdc	
VEBO	6.0	Vdc	
IC	300	mAdc	
PD	625 5.0	mW mW/°C	
PD	1.5 12	Watt mW/°C	
TJ, T _{stg}	-55 to +150	°C	
	VCEO VCBO VEBO IC PD PD	VCEO 400 VCBO 450 VEBO 6.0 IC 300 PD 625 5.0 PD 1.5 12	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta}JC$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V(BR)CEO	400	_	Vdc
Collector-Emitter Breakdown Voltage $(I_C = 100 \ \mu Adc, \ V_{BE} = 0)$	V(BR)CES	450	_	Vdc
Collector-Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V(BR)CBO	450	_	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V(BR)EBO	6.0	_	Vdc
Collector Cutoff Current ($V_{CB} = 400 \text{ Vdc}, I_E = 0$)	ІСВО	—	0.1	μAdc
Collector Cutoff Current (V _{CE} = 400 Vdc, V _{BE} = 0)	ICES	—	500	nAdc
Emitter Cutoff Current (VEB = 4.0 Vdc, $I_C = 0$)	IEBO	—	0.1	μAdc

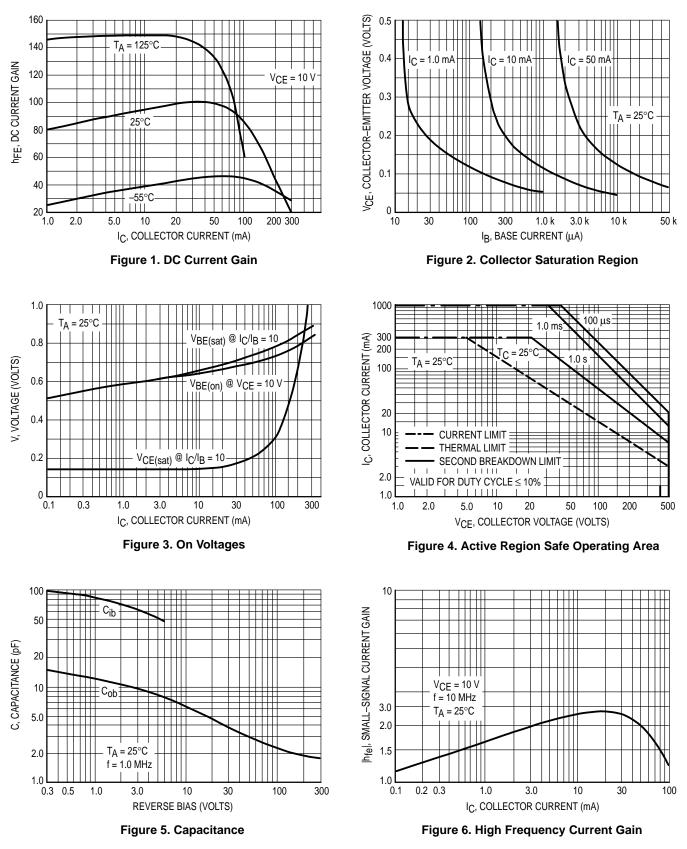
1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

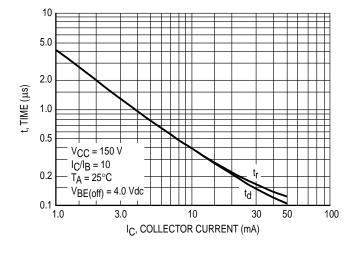


ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS			•	
DC Current Gain ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	hFE	40 50 45 20	 200 	_
Collector-Emitter Saturation Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_B = 0.1 \text{ mAdc}$) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	VCE(sat)		0.4 0.5 0.75	Vdc
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$)	V _{BE(sat)}	_	0.75	Vdc
DYNAMIC CHARACTERISTICS				
High Frequency Current Gain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 20 MHz)	h _{fe}	1.0	_	
Collector–Base Capacitance ($V_{CB} = 20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C _{ob}	_	6.0	pF
Emitter–Base Capacitance (VEB = 0.5 Vdc, I _C = 0 , f = 1.0 MHz)	C _{ib}	_	110	pF
Turn–On Time (V_{CC} = 150 Vdc, $V_{BE(off)}$ = 4.0 V, I _C = 30 mAdc, I _{B1} = 3.0 mAdc)	ton	—	0.6	μs
Turn–Off Time (V _{CC} = 150 Vdc, I_C = 30 mAdc, I_{B1} = I_{B2} = 3.0 mAdc)	toff	—	10	μs

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.





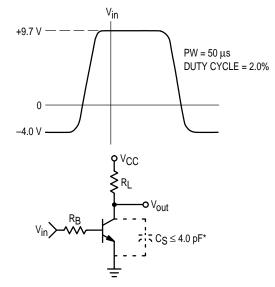


Figure 7. Turn–On Switching Times and Test Circuit

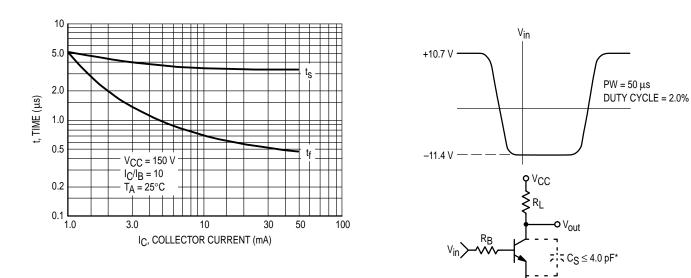
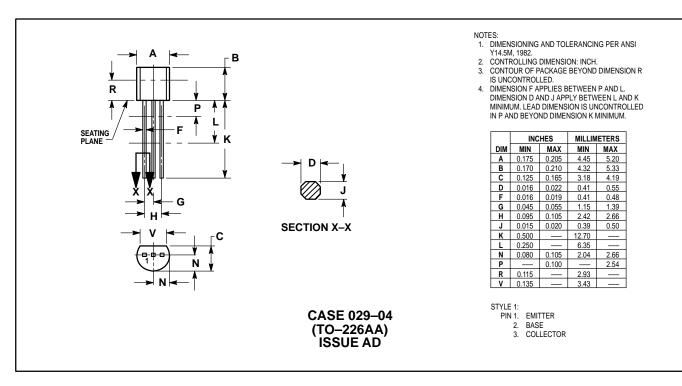


Figure 8. Turn–Off Switching Times and Test Circuit

* Total Shunt Capacitance or Test Jig and Connectors.

÷

PACKAGE DIMENSIONS



BF844

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and **(a)** are registered trademarks of Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447 or 602–303–5454

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE 602-244-6609 INTERNET: http://Design-NET.com JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–81–3521–8315

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298